

Product Summary

V _{(BR)DSS}	R _{DS(ON)}	I _D T _A = +25°C
50V	1.6Ω @ V _{GS} = 10V	500 mA
507	2.5Ω @ V _{GS} = 4.5V	200 mA

Features and Benefits

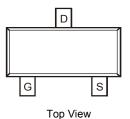
- N-Channel MOSFET
- Low On-Resistance
- Very Low Gate Threshold Voltage
- Low Input Capacitance
- Fast Switching Speed
- Low Input/Output Leakage
- ESD Protected to 2KV
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability

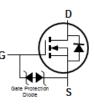
Description and Applications

This MOSFET has been designed to minimize the on-state resistance (R_{DS(ON)}) and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

Mechanical Data

- Case: SOT23
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Matte Tin Finish annealed over Alloy 42 leadframe (Lead Free Plating). Solderable per MIL-STD-202, Method 208 (C3)
- Terminal Connections: See Diagram
- Weight: 0.008 grams (approximate)





Equivalent Circuit

Ordering Information (Note 4)

ESD protected

Part Number	Case	Packaging
DMN53D0L-7	SOT23	3000/Tape & Reel
DMN53D0L-13	SOT23	10000/Tape & Reel

Notes: 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.

Top View

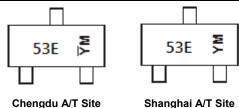
SOT23

2. See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.

3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.

4. For packaging details, go to our website at http://www.diodes.com/products/packages.html.

Marking Information



53E = Product Type Marking Code YM = Date Code Marking for SAT (Shanghai Assembly/ Test site) YM = Date Code Marking for CAT (Chengdu Assembly/ Test site) Y or \overline{Y} = Year (ex: B = 2014) M = Month (ex: 9 = September)

Chengdu A/T Site

Date Code Key		_										
Year	201	4	2015		2016	20	17	2018		2019	2	2020
Code	В		С		D	E	=	F		G		Н
Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	0	N	D



Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Drain Source Voltage	V _{DSS}	50	V
Gate-Source Voltage	V _{GSS}	±20	V
Drain Current (Note 6)	I _D	500	mA

Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Total Power Dissipation (Note 5)	PD	370	mW
Thermal Resistance, Junction to Ambient (Note 5)	R _{0JA}	344	°C/W
Total Power Dissipation (Note 6)	PD	540	mW
Thermal Resistance, Junction to Ambient (Note 6)	R _{θJA}	236	°C/W
Operating and Storage Temperature Range	T _J , T _{STG}	-55 to +150	°C

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

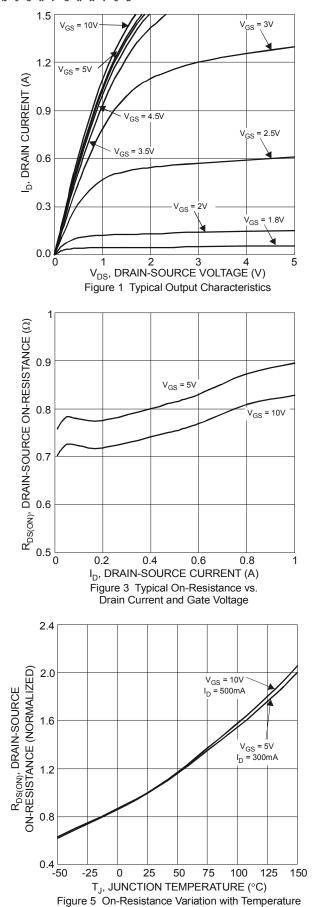
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 7)				Į	I		
Drain-Source Breakdown Voltage	BV _{DSS}	50			V	V _{GS} = 0V, I _D = 250µA	
Zero Gate Voltage Drain Current	I _{DSS}	_	_	1.0	μA	V _{DS} = 50V, V _{GS} = 0V	
Gate-Body Leakage	I _{GSS}	_	_	10	μA	V_{GS} = ±20V, V_{DS} = 0V	
ON CHARACTERISTICS (Note 7)							
Gate Threshold Voltage	V _{GS(th)}	0.8		1.5	V	V_{DS} = V_{GS} , I_D = 250 μ A	
Static Drain-Source On-Resistance	R _{DS(ON)}			1.6 2.5 4.5	Ω		
Source-Drain Diode Forward Voltage	V _{SD}	_		1.4	V	V _{GS} = 0V, I _S = 500mA	
DYNAMIC CHARACTERISTICS (Note 8)							
Input Capacitance	C _{iss}		46		pF	V _{DS} = 25V, V _{GS} = 0V f = 1.0MHz	
Output Capacitance	Coss		5.3		pF		
Reverse Transfer Capacitance	C _{rss}	_	4.0		pF		
Total Gate Charge	Qg	—	0.6		nC		
Gate-Source Charge	Q _{gs}	—	0.2		nC	V _{GS} = 4.5V, V _{DS} = 10V, ID = 250mA	
Gate-Drain Charge	Q _{gd}	_	0.1		nC		
Turn-On Delay Time	t _{D(on)}		2.7		ns		
Turn-On Rise Time	tr	_	2.5	_	ns	V _{DD} = 30V, V _{GS} = 10V, R _G = 25Ω, I _D = 200mA	
Turn-Off Delay Time	t _{D(off)}		19	—	ns		
Turn-Off Fall Time	t _f	_	11	_	ns		

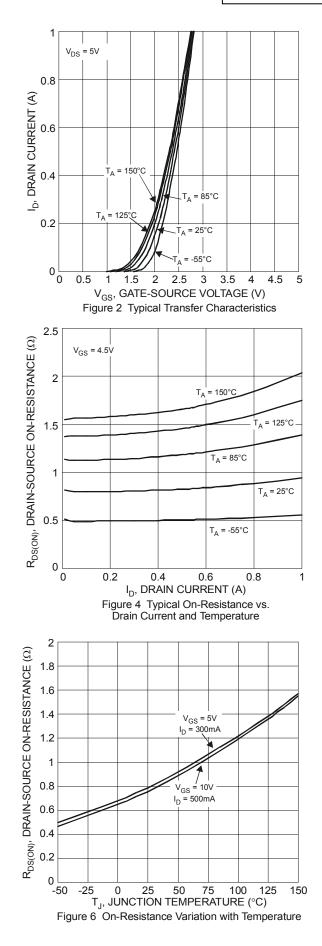
Notes:

Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout
Device mounted on FR-4 substrate PC board, 2oz copper, with thermal vias to bottom layer 1inch square copper plate
Short duration pulse test used to minimize self-heating effect.
Guaranteed by design. Not subject to product testing.



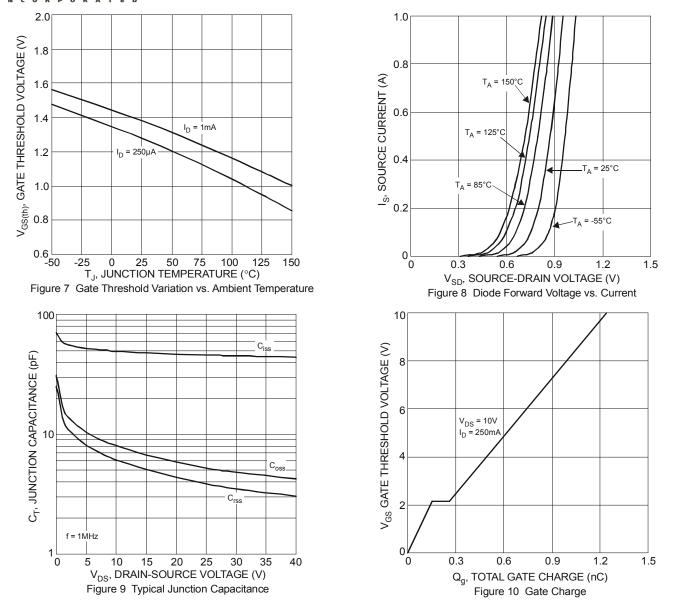






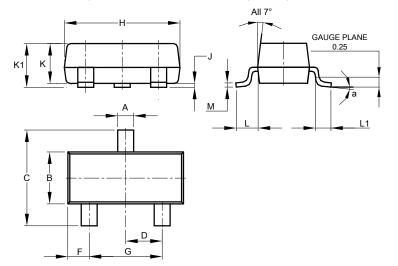
DMN53D0L





Package Outline Dimensions

Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for latest version.

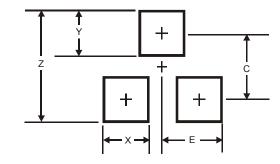


SOT23							
Dim	Min	Max	Тур				
Α	0.37	0.51	0.40				
В	1.20	1.40	1.30				
С	2.30	2.50	2.40				
D	0.89	1.03	0.915				
F	0.45	0.60	0.535				
G	1.78	2.05	1.83				
Н	2.80	3.00	2.90				
J	0.013	0.10	0.05				
К	0.890	1.00	0.975				
K1	0.903	1.10	1.025				
L	0.45	0.61	0.55				
L1	0.25	0.55	0.40				
Μ	0.085	0.150	0.110				
α	8°						
All	All Dimensions in mm						



Suggested Pad Layout

Please see AP02001 at http://www.diodes.com/datasheets/ap02001.pdf for the latest version.



Dimensions	Value (in mm)
Z	2.9
Х	0.8
Y	0.9
С	2.0
E	1.35

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